

## **Radiation-Induced Trap Spectroscopy in Si Bipolar Transistors and GaAs Diodes**

*Monday 3 June 2013 09:20 (30 minutes)*

We have used deep level trap spectroscopy (DLTS) to study neutron, ion and electron induced traps in Si bipolar transistors and in GaAs diodes. We are specifically interested in the effects of defect clustering on transistor gain as well as correlation of specific defects with device gain.

**Primary author:** Dr FLEMING, Robert M. (Sandia National Laboratories, , Albuquerque, NM 87185)

**Presenter:** Dr FLEMING, Robert M. (Sandia National Laboratories, , Albuquerque, NM 87185)

**Session Classification:** Session I